

RECENT ADVANCEMENTS IN
GALLIUM ARSENIDE DEVICES
(PANEL)

This panel will discuss recent work done on three devices which are presently in the forefront of microwave technology. These devices are the GaAs IMPATT diodes for X and Ka-band, Gunn diodes for X and Ka-band, and Field Effect Transistors for C and X-band. Discussion by the panel will include a short presentation by each panel member highlighting recent advancements in his area. Presentations will include discussion of the basic devices and applications of devices. The panel will conclude with a summary of projected performance for the IMPATT, Gunn and FET devices.

Panel Moderator: Gary L. McCoy, Air Force Avionics Laboratory,
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Panel Members:

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Palo Alto, California

Berlin Fank, Varian Solid State West
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C. K. Kim, Special Microwave Device Operation
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